

DATA SHEET

BFG410W NPN 22 GHz wideband transistor

Product specification
Supersedes data of 1997 Oct 29
File under Discrete Semiconductors, SC14

1998 Mar 11

NPN 22 GHz wideband transistor

BFG410W

FEATURES

- Very high power gain
- Low noise figure
- High transition frequency
- Emitter is thermal lead
- Low feedback capacitance.

APPLICATIONS

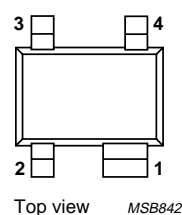
- RF front end
- Wideband applications, e.g. analog and digital cellular telephones, cordless telephones (PHS, DECT, etc.)
- Radar detectors
- Pagers
- Satellite television tuners (SATV)
- High frequency oscillators.

DESCRIPTION

NPN double polysilicon wideband transistor with buried layer for low voltage applications in a plastic, 4-pin dual-emitter SOT343R package.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	emitter
4	collector



Marking code: P4.

Fig.1 Simplified outline SOT343R.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	10	V
V_{CEO}	collector-emitter voltage	open base	–	–	4.5	V
I_C	collector current (DC)		–	10	12	mA
P_{tot}	total power dissipation	$T_s \leq 110\text{ °C}$	–	–	54	mW
h_{FE}	DC current gain	$I_C = 10\text{ mA}; V_{CE} = 2\text{ V}; T_j = 25\text{ °C}$	50	80	120	
C_{re}	feedback capacitance	$I_C = 0; V_{CB} = 2\text{ V}; f = 1\text{ MHz}$	–	45	–	fF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 2\text{ V}; f = 2\text{ GHz}; T_{amb} = 25\text{ °C}$	–	22	–	GHz
G_{max}	maximum power gain	$I_C = 10\text{ mA}; V_{CE} = 2\text{ V}; f = 2\text{ GHz}; T_{amb} = 25\text{ °C}$	–	21	–	dB
F	noise figure	$I_C = 1\text{ mA}; V_{CE} = 2\text{ V}; f = 2\text{ GHz}; \Gamma_S = \Gamma_{opt}$	–	1.2	–	dB

CAUTION

This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A and SNW-FQ-302B.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	10	V
V _{CEO}	collector-emitter voltage	open base	–	4.5	V
V _{EBO}	emitter-base voltage	open collector	–	1	V
I _C	collector current (DC)		–	12	mA
P _{tot}	total power dissipation	T _s ≤ 110 °C; note 1; see Fig.2	–	54	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	operating junction temperature		–	150	°C

Note

1. T_s is the temperature at the soldering point of the emitter pins.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-s}	thermal resistance from junction to soldering point	750	K/W

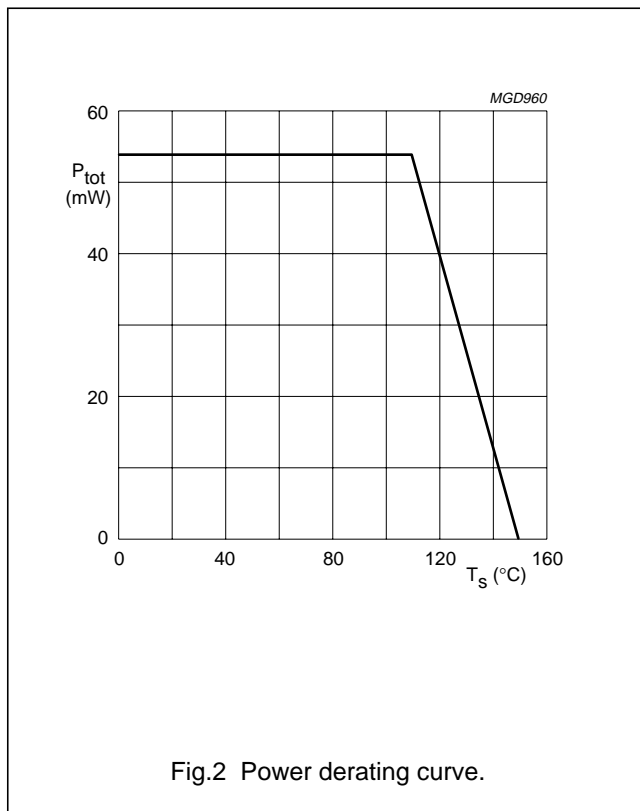


Fig.2 Power derating curve.

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CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

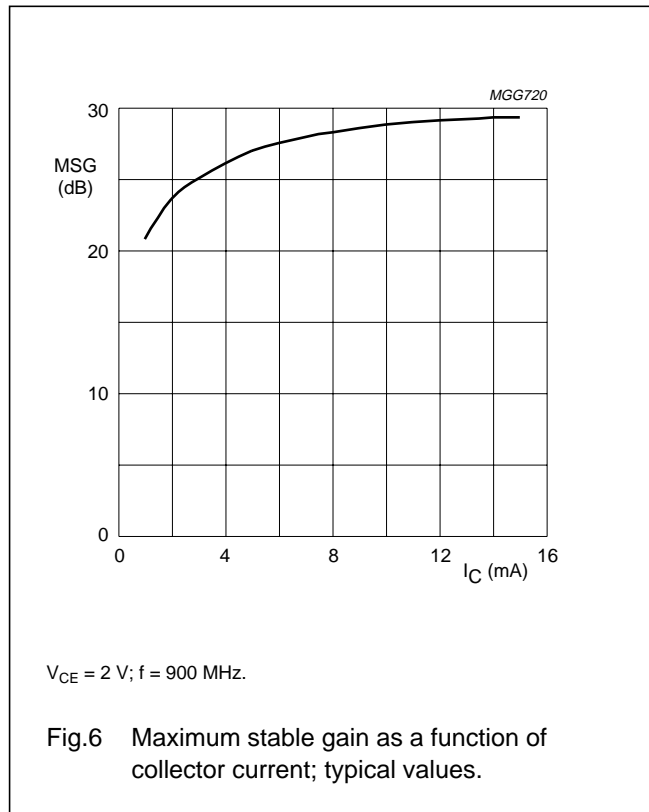
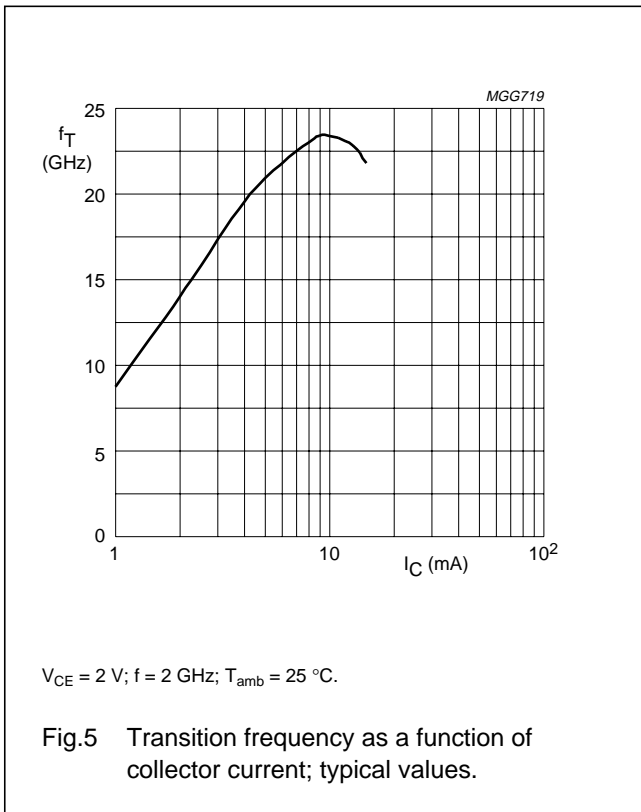
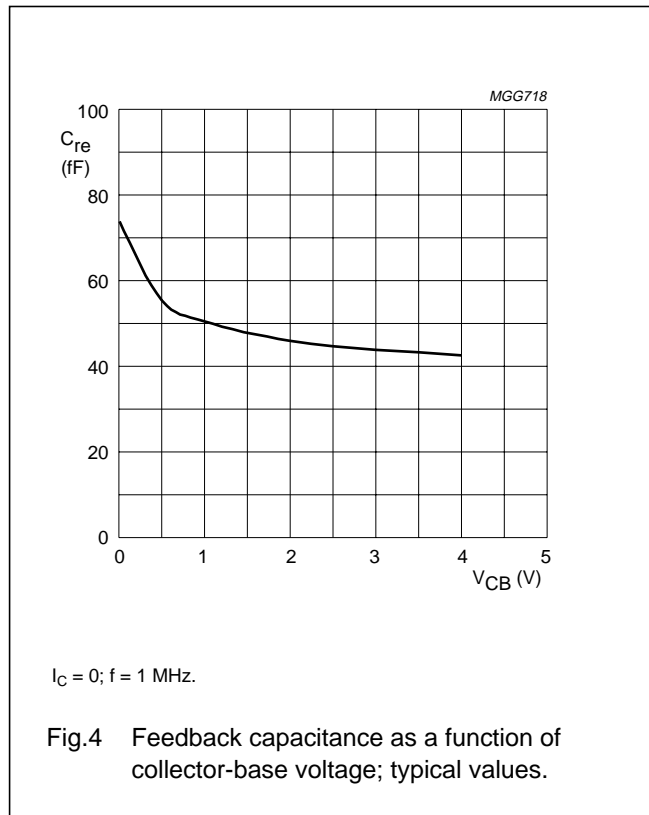
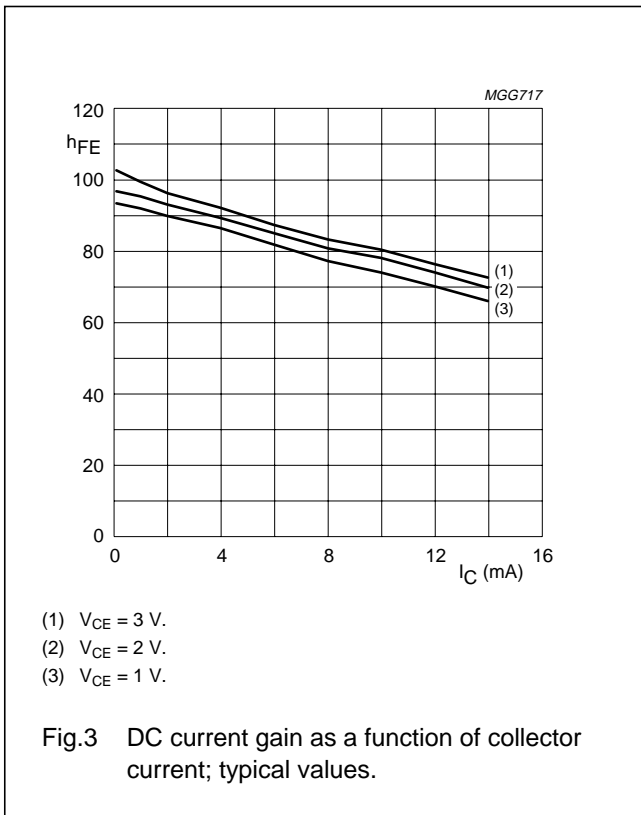
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 2.5\ \mu\text{A}; I_E = 0$	10	–	–	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 1\ \text{mA}; I_B = 0$	4.5	–	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = 2.5\ \mu\text{A}; I_C = 0$	1	–	–	V
I_{CBO}	collector-base leakage current	$I_E = 0; V_{CB} = 4.5\ \text{V}$	–	–	15	nA
h_{FE}	DC current gain	$I_C = 10\ \text{mA}; V_{CE} = 2\ \text{V};$ see Fig.3	50	80	120	
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = 2\ \text{V}; f = 1\ \text{MHz}$	–	220	–	fF
C_e	emitter capacitance	$I_C = i_c = 0; V_{EB} = 0.5\ \text{V}; f = 1\ \text{MHz}$	–	400	–	fF
C_{re}	feedback capacitance	$I_C = 0; V_{CB} = 2\ \text{V}; f = 1\ \text{MHz};$ see Fig.4	–	45	–	fF
f_T	transition frequency	$I_C = 10\ \text{mA}; V_{CE} = 2\ \text{V}; f = 2\ \text{GHz};$ $T_{amb} = 25\text{ °C};$ see Fig.5	–	22	–	GHz
G_{max}	maximum power gain; note 1	$I_C = 10\ \text{mA}; V_{CE} = 2\ \text{V}; f = 2\ \text{GHz};$ $T_{amb} = 25\text{ °C};$ see Figs 7 and 8	–	21	–	dB
$ S_{21} ^2$	insertion power gain	$I_C = 10\ \text{mA}; V_{CE} = 2\ \text{V}; f = 2\ \text{GHz};$ $T_{amb} = 25\text{ °C};$ see Fig.8	–	18	–	dB
F	noise figure	$I_C = 1\ \text{mA}; V_{CE} = 2\ \text{V};$ $f = 900\ \text{MHz}; \Gamma_S = \Gamma_{opt};$ see Fig.13	–	0.9	–	dB
		$I_C = 1\ \text{mA}; V_{CE} = 2\ \text{V}; f = 2\ \text{GHz};$ $\Gamma_S = \Gamma_{opt};$ see Fig.13	–	1.2	–	dB
P_{L1}	output power at 1 dB gain compression	$I_C = 10\ \text{mA}; V_{CE} = 2\ \text{V}; f = 2\ \text{GHz};$ $Z_S = Z_{S\ opt}; Z_L = Z_{L\ opt};$ note 2	–	5	–	dBm
ITO	third order intercept point	$I_C = 10\ \text{mA}; V_{CE} = 2\ \text{V}; f = 2\ \text{GHz};$ $Z_S = Z_{S\ opt}; Z_L = Z_{L\ opt};$ note 2	–	15	–	dBm

Notes

- G_{max} is the maximum power gain, if $K > 1$. If $K < 1$ then $G_{max} = \text{MSG}$; see Figs 6, 7 and 8.
- Z_S is optimized for noise; Z_L is optimized for gain.

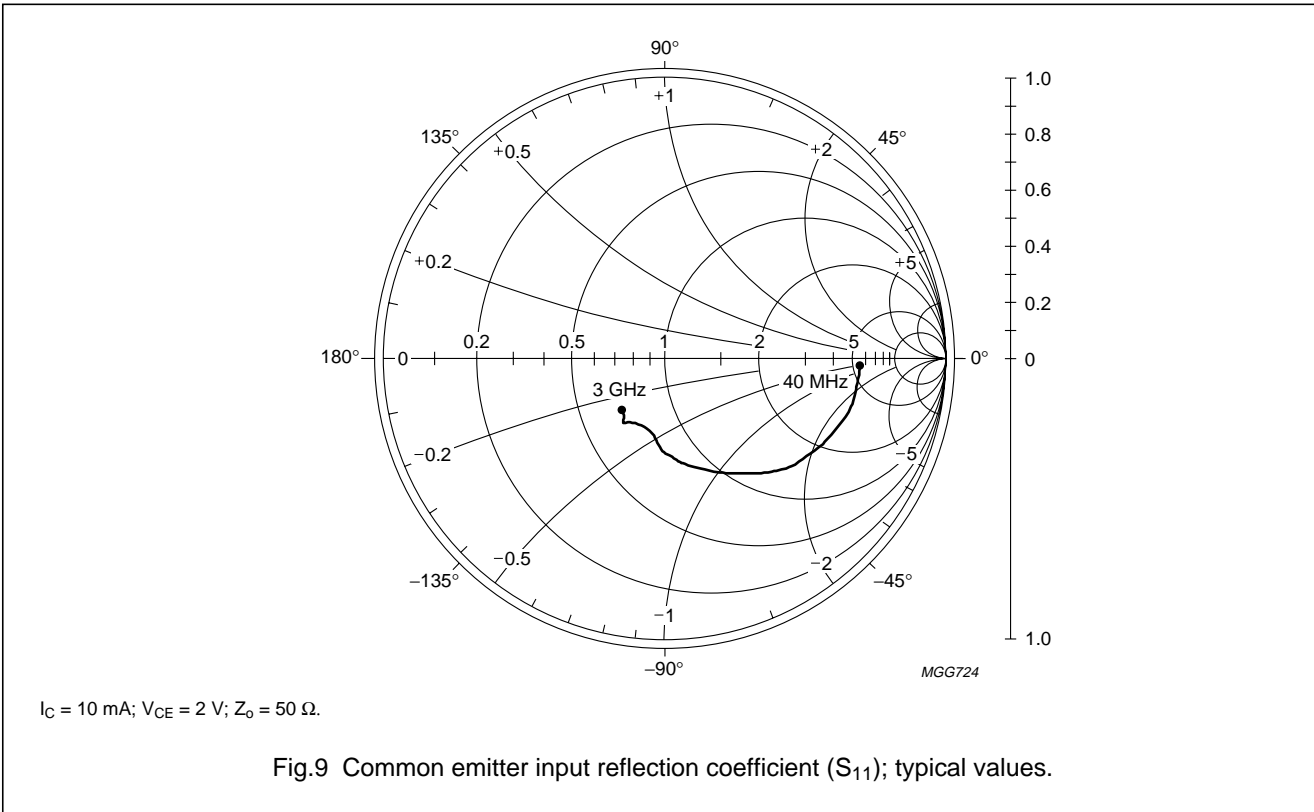
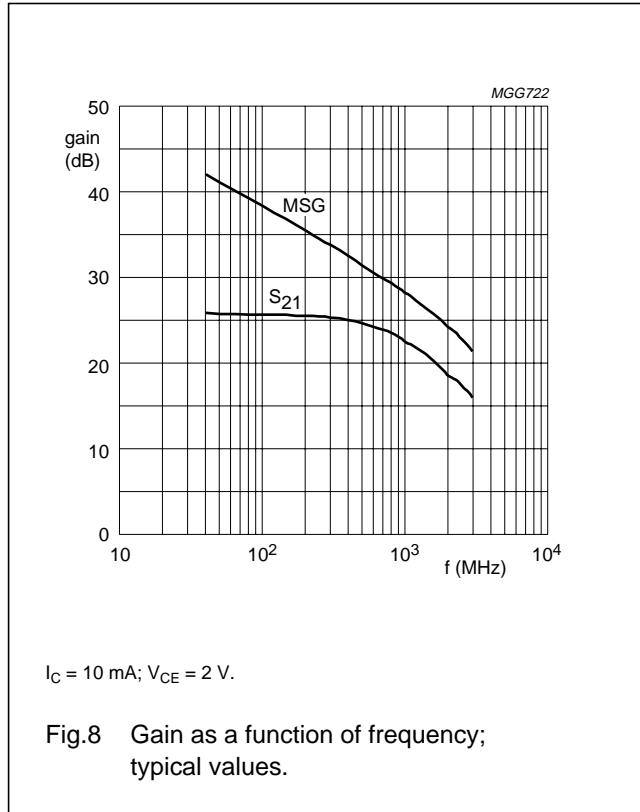
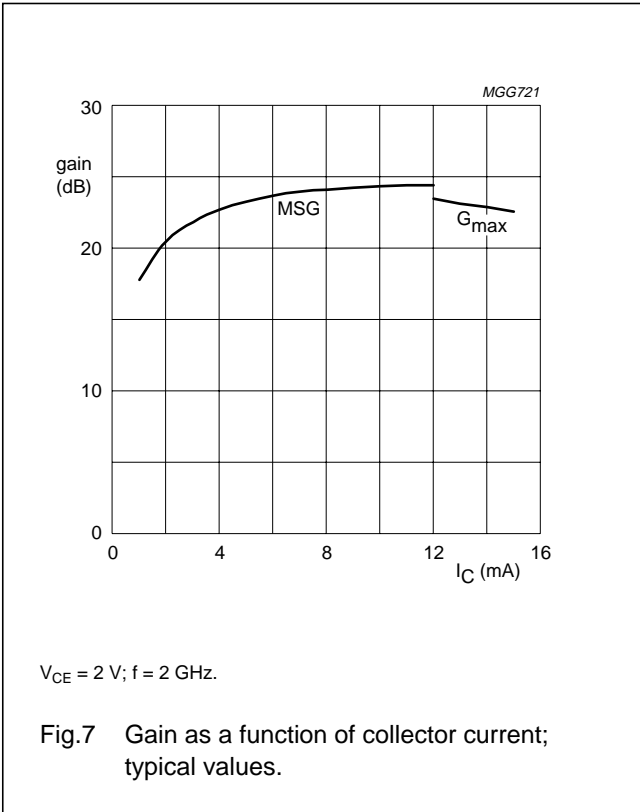
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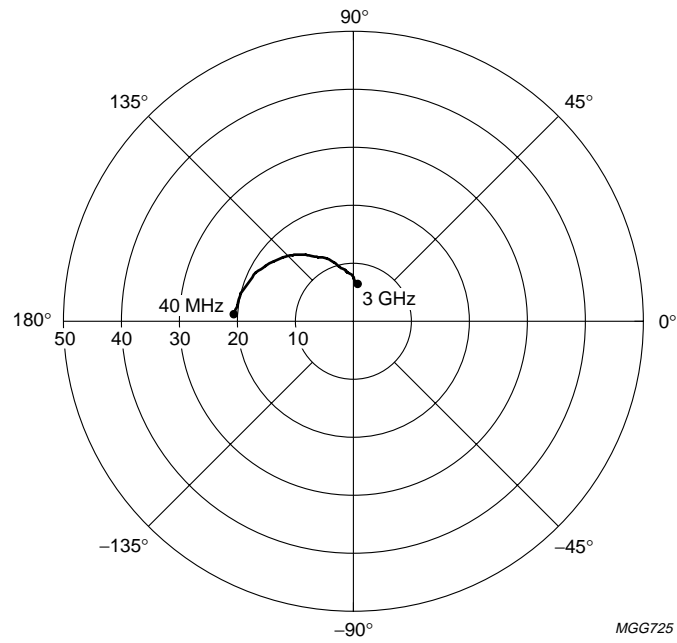
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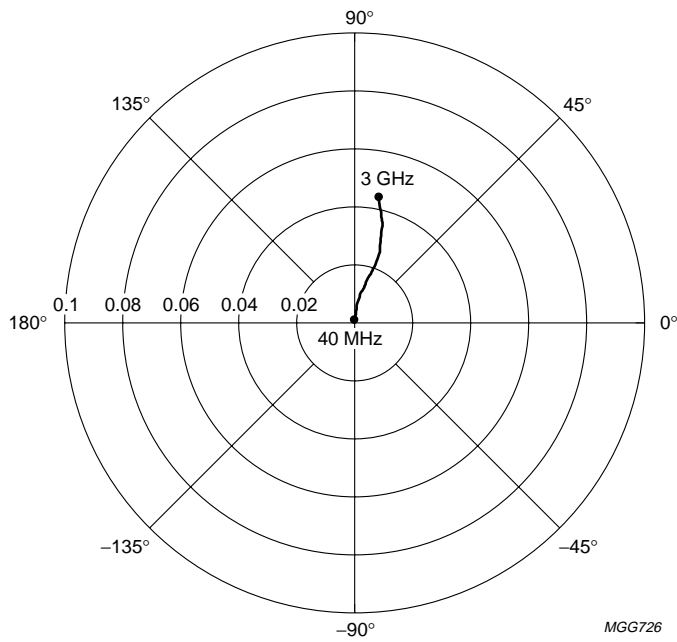
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$I_C = 10 \text{ mA}; V_{CE} = 2 \text{ V}.$

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Fig.10 Common emitter forward transmission coefficient (S_{21}); typical values.



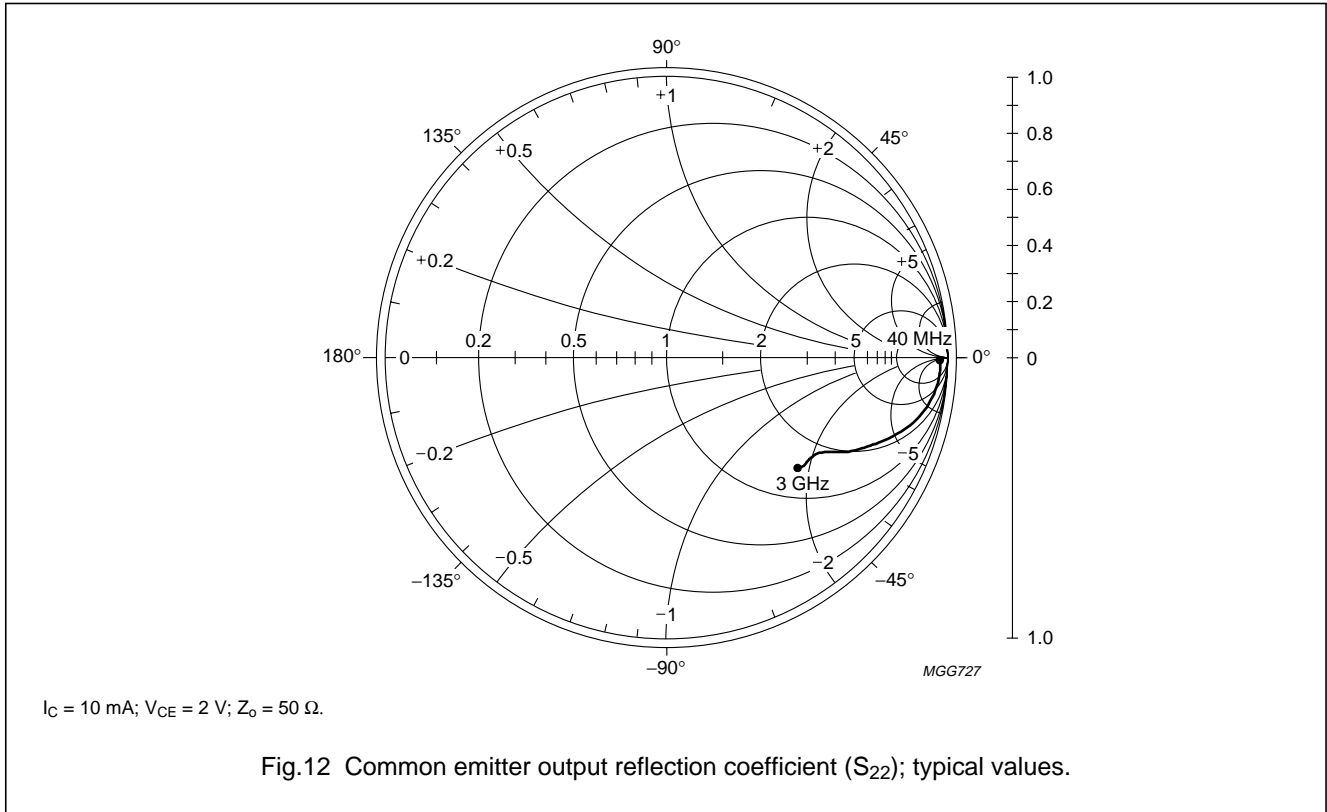
$I_C = 10 \text{ mA}; V_{CE} = 2 \text{ V}.$

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Fig.11 Common emitter reverse transmission coefficient (S_{12}); typical values.

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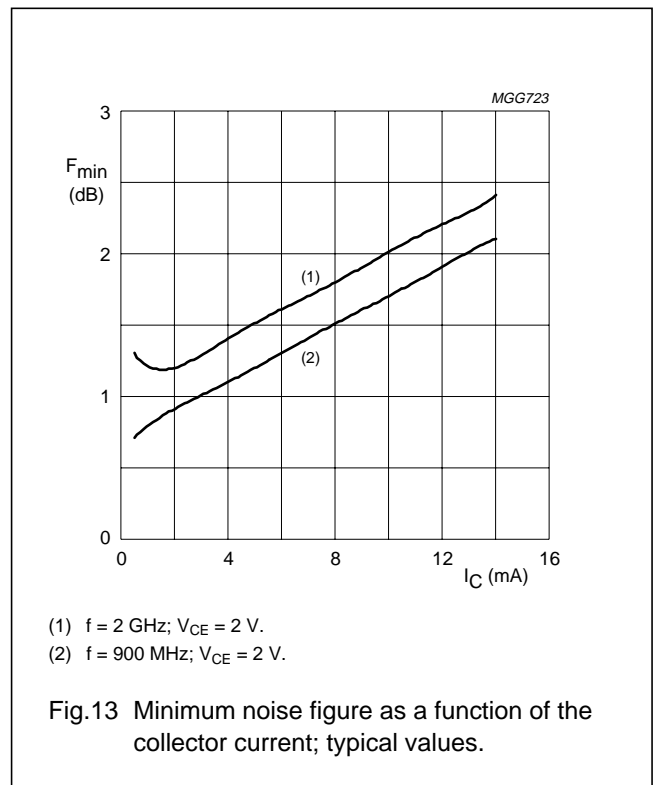
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Noise data

$V_{CE} = 2 \text{ V}$; typical values.

f (MHz)	I_C (mA)	F_{min} (dB)	Γ_{mag}	Γ_{angle}	r_n (Ω)
900	1	0.8	0.73	11.2	0.56
	2	0.9	0.58	10.1	0.43
	4	1.1	0.40	10.1	0.33
	6	1.3	0.28	11.0	0.30
	8	1.5	0.20	8.0	0.30
	10	1.7	0.14	10.5	0.27
	12	1.9	0.06	10.1	0.25
	14	2.1	0.05	14.2	0.26
2000	1	1.2	0.64	35.7	0.57
	2	1.2	0.50	35.8	0.44
	4	1.4	0.34	34.4	0.37
	6	1.6	0.25	33.7	0.34
	8	1.8	0.17	34.5	0.35
	10	2.0	0.12	35.8	0.34
	12	2.2	0.05	38.0	0.35
	14	2.4	0.03	44.8	0.34



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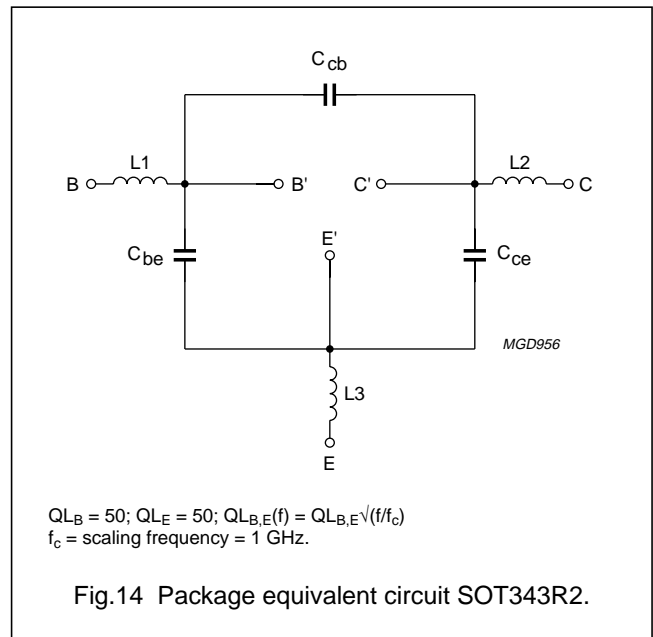
SPICE parameters for the BFG410W die

SEQUENCE No.	PARAMETER	VALUE	UNIT
1	IS	19.42	aA
2	BF	145.0	–
3	NF	0.993	–
4	VAF	31.12	V
5	IKF	125.0	mA
6	ISE	123.6	fA
7	NE	3.000	–
8	BR	11.37	–
9	NR	0.985	–
10	VAR	1.874	V
11	IKR	50.00	mA
12	ISC	199.6	aA
13	NC	1.546	–
14	RB	35.00	Ω
15	IRB	0.000	A
16	RBM	15.00	Ω
17	RE	432.0	m Ω
18	RC	4.324	Ω
19 (1)	XTB	1.500	–
20 (1)	EG	1.110	eV
21 (1)	XTI	3.000	–
22	CJE	128.0	fF
23	VJE	900.0	mV
24	MJE	0.346	–
25	TF	4.122	ps
26	XTF	68.20	–
27	VTF	2.004	V
28	ITF	0.627	A
29	PTF	0.000	deg
30	CJC	56.68	fF
31	VJC	556.9	mV
32	MJC	0.207	–
33	XCJC	0.500	–
34 (1)	TR	0.000	ns
35 (1)	CJS	274.8	fF
36 (1)	VJS	418.3	mV
37 (1)	MJS	0.239	–
38	FC	0.550	–

SEQUENCE No.	PARAMETER	VALUE	UNIT
39 (2)(3)	C _{bp}	145	fF
40 (2)	R _{sb1}	25	Ω
41 (3)	R _{sb2}	19	Ω

Notes

1. These parameters have not been extracted, the default values are shown.
2. Bonding pad capacity C_{bp} in series with substrate resistance R_{sb1} between B' and E'.
3. Bonding pad capacity C_{bp} in series with substrate resistance R_{sb2} between C' and E'.



List of components (see Fig.14)

DESIGNATION	VALUE	UNIT
C _{be}	80	fF
C _{cb}	2	fF
C _{ce}	80	fF
L1	1.1	nH
L2	1.1	nH
L3 (note 1)	0.25	nH

Note

1. External emitter inductance to be added separately due to the influence of the printed-circuit board.

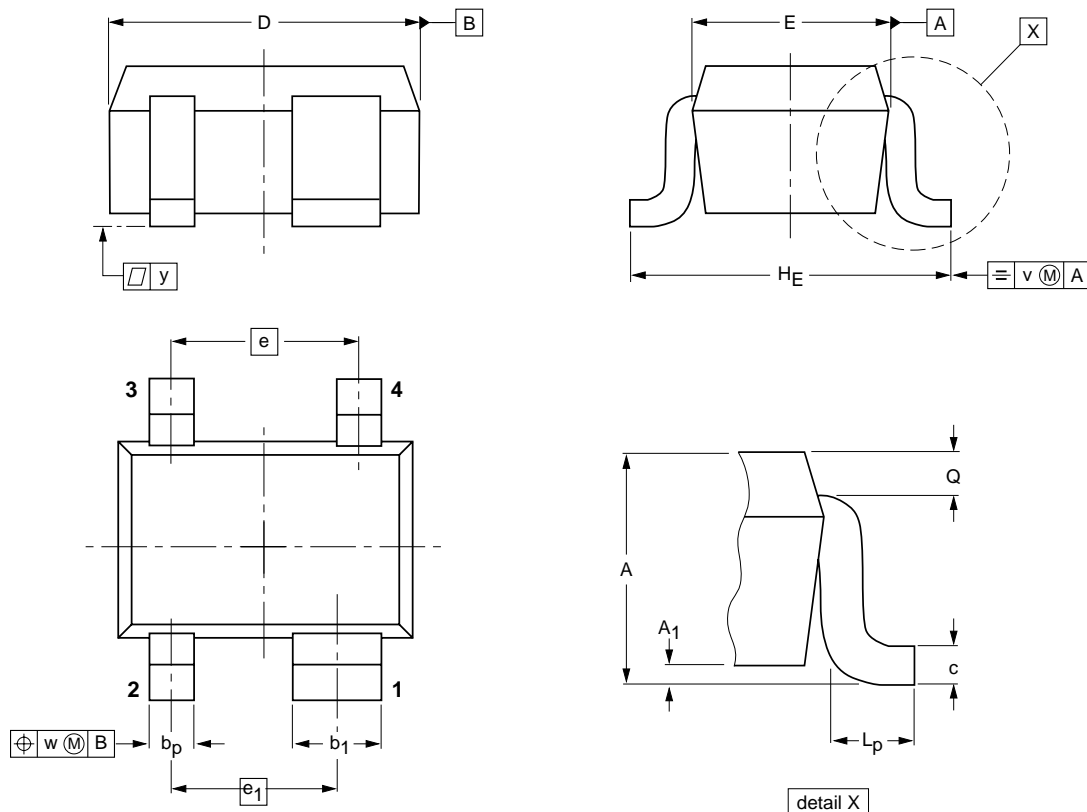
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PACKAGE OUTLINE

Plastic surface mounted package; reverse pinning; 4 leads

SOT343R



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	b ₁	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.8	0.1	0.4 0.3	0.7 0.5	0.25 0.10	2.2 1.8	1.35 1.15	1.3	1.15	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT343R						97-05-21

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DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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微波光电部专业代理经销高频、微波、光纤、光电元器件、组件、部件、模块、整机；电磁兼容元器件、材料、设备；微波 CAD、EDA 软件、开发测试仿真工具；微波、光纤仪器仪表。欢迎国外高科技微波、光纤厂商将优秀产品介绍到中国、共同开拓市场。长期大量现货专业批发高频、微波、卫星、光纤、电视、CATV 器件：晶振、VCO、连接器、PIN 开关、变容二极管、开关二极管、低噪晶体管、功率电阻及电容、放大器、功率管、MMIC、混频器、耦合器、功分器、振荡器、合成器、衰减器、滤波器、隔离器、环行器、移相器、调制解调器；光电子元件和组件：红外发射管、红外接收管、光电开关、光敏管、发光二极管和发光二极管组件、半导体激光二极管和激光器组件、光电探测器和光接收组件、光发射接收模块、光纤激光器和光放大器、光调制器、光开关、DWDM 用光发射和接收器件、用户接入系统光收发器件与模块、光纤连接器、光纤跳线/尾纤、光衰减器、光纤适配器、光隔离器、光耦合器、光环行器、光复用器/转换器；无线收发芯片和模组、蓝牙芯片和模组。

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